



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16522Generic Copy

Issue Date: 24-Sep-2010

TITLE: Final Notification for Transfer of the Bipolar Power Epi Base, Bipolar Power Base Technologies, TVS (Transient Voltage Suppressor) Arrays and Ultrafast Rectifier from ON Semiconductor ZR Fab in Phoenix (USA) to ON Semiconductor ISMF Fab in Seremban (Malaysia)

PROPOSED FIRST SHIP DATE: 24-Dec-2010

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fab Site

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or following Contact Product Engineers:

FPCN Contact person by Affected Technology:

Bipolar Power Epi Base

Farrah Awang

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Bipolar Power Base Technology

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Ultrafast Rectifier Technology

Raja Roziah

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TVS Array

Huey Shan Wong

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SAMPLES: Contact your local ON Semiconductor Sales Office or contacts listed above.

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Laura Rivers <laura.rivers@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

ON Semiconductor is notifying customers of its plan to transfer Bipolar Power Epi Base and Bipolar Power Base Technologies and Ultrafast Rectifier from ON Semiconductor ZR Fab in Phoenix (USA) to ON Semiconductor ISMF Fab in Seremban (Malaysia).

The ISMF facility is an ON Semiconductor owned wafer fab that has been producing products for ON Semiconductor since 1998. Several existing technologies within ON Semiconductor's product families are currently sourced from ISMF, including Zener Diodes, Small Signal Diodes, Small Signal Bipolar Transistor, and USB array filter products. ON Semiconductor Seremban Wafer FAB is an internal factory that is TS16949, ISO-9001 and ISO-14000 certified.



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Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

Products listed in this final PCN should be transferred to ON Semiconductor ISMF Fab in Seremban (Malaysia) starting 13th December 2010. After 13th December 2010, customer may receive products from either facility.

QUALIFICATION PLAN:

Reliability testing was performed on qualification vehicles chosen based on die size, voltage rating, and run rates.

RELIABILITY DATA SUMMARY FOR BIPOLAR POWER EPI BASE:

Package: Dpak
Qual Vehicles:
MJD42CG

| Test: | Conditions: | Interval: | Results |
|--------------|---|-----------|---------|
| HTRB | TA=150C, 80% Rated Voltage | 1008 hrs | 0/80 |
| Autoclave+PC | Ta=121C RH=100% ~15 psig | 96 hrs | 0/80 |
| H3TRB+PC | Ta=85C RH=85% | 1008 hrs | 0/80 |
| | bias=80% rated V or 100V Max | | |
| IOL+PC | Ta=25C, Delta TJ = 100 C, Ton/off = 2 min. | 15000 cyc | 0/80 |
| TC+PC | Ta= -65 C to 150 C | 1000 cyc | 0/80 |
| RSH | Ta=260C, 10 sec dwell | | 0/30 |
| DPA | post TC | | 0/2 |
| DPA | post H3TRB | | 0/2 |

Package: Dpak
MJD122G

| Test: | Conditions: | Interval: | Results |
|--------------|---|-----------|---------|
| HTRB | TA=150C, 80% Rated Voltage | 1008 hrs | 0/160 |
| Autoclave+PC | Ta=121C RH=100% ~15 psig | 96 hrs | 0/160 |
| H3TRB+PC | Ta=85C RH=85% | 1008 hrs | 0/160 |
| | bias=80% rated V or 100V Max | | |
| IOL+PC | Ta=25C, Delta TJ = 100 C, Ton/off = 2 min. | 15000 cyc | 0/160 |
| TC+PC | Ta= -65 C to 150 C | 1000 cyc | 0/160 |
| RSH | Ta=260C, 10 sec dwell | | 0/30 |
| DPA | post TC | | 0/4 |
| DPA | post H3TRB | | 0/4 |


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RELIABILITY DATA SUMMARY FOR BIPOLAR POWER POWER BASE:

Qual Vehicles:

MJW21194G

Package: TO247

| Test: | Conditions: | Interval: | Results |
|--------------|---|-----------|---------|
| HTRB | Ta=150C,80% Rated Voltage | 504 hrs | 0/160 |
| Autoclave+PC | Ta=121C RH=100% ~15 psig | 96 hrs | 0/160 |
| H3TRB+PC | Ta=85C RH=85% bias=80% rated V or100V Max | 504 hrs | 0/160 |
| IOL+PC | Ta=25C, Delta TJ = 100 C, Ton/off = 5 min. | 3000 cyc | 0/160 |
| TC+PC | Ta= -65 C to 150 C | 1000 cyc | 0/160 |
| RSH | Ta=260C, 10 sec dwell | | 0/30 |
| DPA | post TC | | 0/4 |

MJ21193G

Package: TO-3

| Test: | Conditions: | Interval: | Results |
|--------|---|-----------|---------|
| HTRB | TA=150C,80% Rated Voltage | 1008 hrs | 0/80 |
| IOL+PC | Ta=25C, Delta TJ = 100 C, Ton/off = 2 min. | 5000 cyc | 0/77 |
| TC+PC | Ta= -65 C to 150 C | 1000 cyc | 0/77 |

RELIABILITY DATA SUMMARY FOR ULTRAFAST RECTIFIER:

Package: 3A Axial

Qual Vehicle: MUR4100E Rectifier

| Test | Condition | Interval | Results |
|-----------|---|-----------|---------|
| HTRB | Tj=150C,80% Rated Voltage | 168 hrs | 0/231 |
| Autoclave | Ta=121C RH=100% ~15 psig | 96 hrs | 0/231 |
| H3TRB | Ta=85C RH=85% bias=80% rated V or100V Max | 1008 hrs | 0/231 |
| IOL | Ta=25C, Delta TJ = 100 C, Ton/off = 2 min. | 15000 cyc | 0/231 |
| TC | Ta= -65 C to 150 C | 1000 cyc | 0/231 |
| RSH | Ta=260C, 10 sec dwell | | 0/30 |

Package: TO220

MUR8100E Rectifier

| Test | Condition | Interval | Results |
|------|----------------------------|----------|---------|
| HTRB | Tj=150C, 80% Rated Voltage | 168 hrs | 0/80 |

**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16522****RELIABILITY DATA SUMMARY FOR TVS Array:**

Package: SO-8

Qual Vehicles:

NUP4201DR2G

Test:

| | Conditions: | Interval: | Results |
|--------------|--|-----------|---------|
| HTRB | Ta=150C, 80% Rated Voltage | 504 hrs | 0/231 |
| Autoclave+PC | Ta=121C RH=100% ~15 psig | 96 hrs | 0/231 |
| HAST+PC | Ta=130C RH=85% bias=80% rated V or 100V Max | 96 hrs | 0/231 |
| TC+PC | Ta= -65 C to 150 C | 1000 cyc | 0/231 |
| RSH | Ta=260C, 10 sec dwell | | 0/30 |
| DPA | post TC | | 0/6 |
| DPA | post HAST | | 0/6 |

ELECTRICAL CHARACTERISTIC SUMMARY:

Available upon request

CHANGED PART IDENTIFICATION:

Affected products from ON Semiconductor with date code 1051 representing WW51, 2010 and greater may be sourced from either the ISMF Fab in Seremban (Malaysia) or the ZR Fab in Phoenix (USA).


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List of affected General Parts

| Ultrafast Rectifier: | | |
|-----------------------------|-------------|--------------|
| MURS480ET3G | MUR180EG | MUR880EG |
| MUR480EG | MUR180ERLG | MUR8100EG |
| MUR480ERLG | MUR1100EG | MUR8100EH |
| MUR480ESG | MUR1100ERLG | MURC8100EWP |
| MUR4100EG | MUR2100EG | SUR84100ERLG |
| MUR4100ERLG | MUR2100ERLG | |

| Bipolar Power Epi Base Technology: | | |
|---|------------|---------------|
| 2N3055AG | BD810G | MJF31CG |
| 2N3055G | BDV64BG | MJF32CG |
| 2N3442G | BDV65BG | MJF6388G |
| 2N3771G | BDW42G | MJH6284G |
| 2N3772G | BDW46G | MJH6287G |
| 2N3773G | BDW47G | NJV2N6045G |
| 2N4918G | BDX34BG | NJV2N6107G |
| 2N4919G | BDX34CG | NJV2N6109G |
| 2N4920G | BDX54BG | NJVMJ11028G |
| 2N4921G | BDX54CG | NJVMJB42CT4G |
| 2N4922G | MJ11012G | NJVMJD112T4G |
| 2N4923G | MJ11015G | NJVMJD117T4G |
| 2N5190G | MJ11016G | NJVMJD122T4G |
| 2N5191G | MJ11028G | NJVMJD128T4G |
| 2N5192G | MJ11030G | NJVMJD148T4G |
| 2N5194G | MJ11032G | NJVMJD2955T4G |
| 2N5195G | MJ11033G | NJVMJD31CT4G |
| 2N5302G | MJ14002G | NJVMJD32CT4G |
| 2N5684G | MJ15001G | NJVMJD41CT4G |
| 2N5686G | MJ15015G | NJVMJD42CRLG |
| 2N5883G | MJ15016G | NJVMJD42CT4G |
| 2N5884G | MJ2955G | NJVTIP122G |
| 2N5885G | MJ4502G | NJVTIP31CG |
| 2N5886G | MJ802G | NJVTIP32BG |
| 2N6034G | MJB41CG | NJVTIP32CG |
| 2N6035G | MJB41CT4G | NJVTIP36CG |
| 2N6036G | MJB42CT4G | NJVTIP41CG |
| 2N6038G | MJC11015WP | NJVTIP42CG |
| 2N6039G | MJC11016WP | SJD112T4G |
| 2N6040G | MJD112-1G | SJD127T4 |
| 2N6042G | MJD112G | SJD127T4G |
| 2N6043G | MJD112RLG | SJD32CT4 |
| 2N6045G | MJD112T4G | SJD32CT4G |
| 2N6052G | MJD117-1G | TIP100G |
| 2N6107G | MJD117G | TIP101G |
| 2N6109G | MJD117RLG | TIP102G |
| 2N6111G | MJD117T4G | TIP106G |
| 2N6284G | MJD122G | TIP107G |
| 2N6286G | MJD122T4G | TIP110G |


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| Bipolar Power Epi Base Technology: | | |
|---|------------|----------|
| 2N6287G | MJD127G | TIP111G |
| 2N6288G | MJD127T4 | TIP112G |
| 2N6292G | MJD127T4G | TIP115G |
| 2N6487G | MJD128T4G | TIP116G |
| 2N6488G | MJD148T4 | TIP117G |
| 2N6490G | MJD148T4G | TIP120G |
| 2N6491G | MJD2955-1G | TIP121G |
| 2N6667G | MJD2955G | TIP122G |
| BD179G | MJD2955T4G | TIP125G |
| BD180G | MJD3055G | TIP126G |
| BD234G | MJD3055T4G | TIP127G |
| BD237G | MJD31C1G | TIP140G |
| BD241CG | MJD31CG | TIP141G |
| BD242BG | MJD31CRLG | TIP142G |
| BD242CG | MJD31CT4G | TIP147G |
| BD243CG | MJD31T4G | TIP2955G |
| BD244BG | MJD32CG | TIP29AG |
| BD244CG | MJD32CRLG | TIP29BG |
| BD435G | MJD32CT4 | TIP29CG |
| BD436TG | MJD32CT4G | TIP3055G |
| BD437G | MJD32RLG | TIP30CG |
| BD437TG | MJD32T4G | TIP31AG |
| BD438G | MJD41CRLG | TIP31BG |
| BD439G | MJD41CT4G | TIP31CG |
| BD440G | MJD42C1G | TIP31G |
| BD441G | MJD42CG | TIP32AG |
| BD442G | MJD42CRLG | TIP32BG |
| BD675AG | MJD42CT4G | TIP32CG |
| BD675G | MJD6039T4G | TIP32G |
| BD676AG | MJE2955TG | TIP33CG |
| BD676G | MJE3055TG | TIP35AG |
| BD677AG | MJE371G | TIP35CG |
| BD677G | MJE4353G | TIP36AG |
| BD678AG | MJE700G | TIP36CG |
| BD678G | MJE702G | TIP41AG |
| BD679AG | MJE703G | TIP41BG |
| BD679G | MJE800G | TIP41CG |
| BD680AG | MJE802G | TIP42AG |
| BD680G | MJE803G | TIP42BG |
| BD681G | MJF122G | TIP42CG |
| BD682G | MJF127G | TIP42G |
| BD682TG | MJF2955G | |
| BD809G | MJF3055G | |


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| Bipolar Power Base Technology: | | |
|---------------------------------------|------------|-----------|
| MJ11021G | MJC11021WP | MJL21195G |
| MJ11022G | MJC11022WP | MJL21196G |
| MJ15003G | MJC15003WP | MJL3281AG |
| MJ15004G | MJC15004WP | MJW21193G |
| MJ15022G | MJE4343G | MJW21194G |
| MJ15023G | MJH11017G | MJW21195G |
| MJ15024G | MJH11019G | MJW21196G |
| MJ15025G | MJH11020G | MJW3281AG |
| MJ21193G | MJH11021G | NJL3281DG |
| MJ21194G | MJH11022G | NJW21193G |
| MJ21195G | MJL21193G | NJW21194G |
| MJ21196G | MJL21194G | NJW3281G |

| TVS Array: | | |
|-------------------|---------|---------------|
| LC03-6R2G | SL05T1G | SRDA05-4R2G |
| NUP4106DR2G | SL15T1G | SL12T1G |
| NUP4201DR2G | SL24T1G | SRDA3.3-4DR2G |



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List of affected Customer Specific Parts

| |
|----------------------------|
| Ultrafast Rectifier |
| SUR456ERLG |

| | | |
|---|----------------|------------|
| Bipolar Power Epi Base Technology: | | |
| TEC0179PF | SJD1001T4G | SJD1023T4G |
| SJ6425-1G | SJD1008LFKBT4G | SJD1029T4 |
| SJB1001T4G | SJD1015-1G | SJD1029T4G |
| SJB1002T4 | SJD1015T4 | SJD31CT4G |
| SJB1002T4G | SJD1015T4G | SJD42CT4G |
| SJD1001T4 | SJD1018RLG | SJE9122G |
| | SJD1023T4 | |

| | | |
|---------------------------------------|---------|----------|
| Bipolar Power Base Technology: | | |
| SJ6521AG | SJ7147G | SJ9622G |
| SJ6522AG | SJ8274G | SJW3281G |